

N-Channel Enhancement Mode Power MOSFET

Description

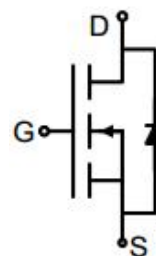
This advanced MOSFET family has optimized on-state resistance, and also provides superior switching performance and higher avalanche energy strength. This device family is suitable for high efficiency switch mode power supplies.

General Features

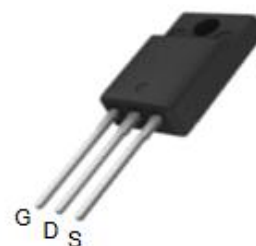
- V_{DS} 900V
- I_D (at $V_{GS} = 10V$) 6A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 3Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220F

Ordering Information

Device	Package	Marking	Packaging
G6N90F	TO-220F	G6N90	50pcs/Tube

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	900	V
Continuous Drain Current	I_D	6	A
Pulsed Drain Current (note1)	I_{DM}	18	A
Gate-Source Voltage	V_{GS}	±30	V
Power Dissipation	P_D	69	W
Single pulse avalanche energy (note2)	E_{AS}	180	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	°C/W
Maximum Junction-to-Case	R_{thJC}	1.8	°C/W

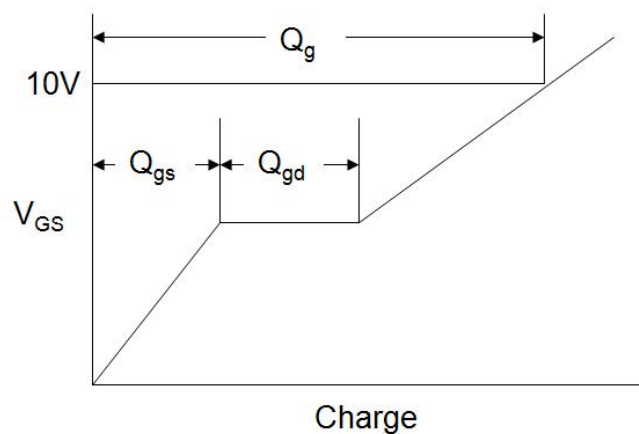
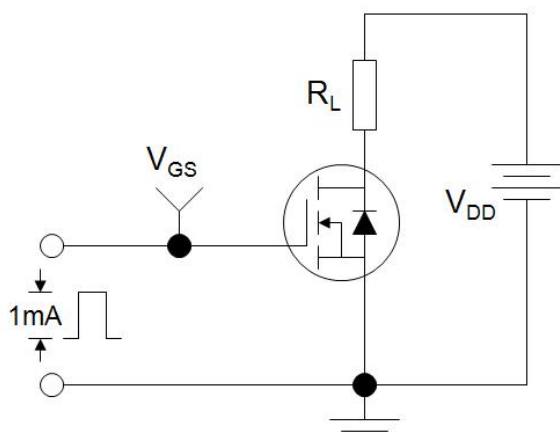
Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	900	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900V, V_{GS} = 0V$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	4.0	5.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$	--	2.5	3	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 450V,$ $f = 1.0MHz$	--	1060	--	pF
Output Capacitance	C_{oss}		--	20	--	
Reverse Transfer Capacitance	C_{rss}		--	2	--	
Total Gate Charge	Q_g	$V_{DD} = 450V,$ $I_D = 3A,$ $V_{GS} = 10V$	--	25	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	
Gate-Drain Charge	Q_{gd}		--	12	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 450V,$ $I_D = 3A,$ $R_G = 25\Omega$	--	68	--	ns
Turn-on Rise Time	t_r		--	30	--	
Turn-off Delay Time	$t_{d(off)}$		--	97	--	
Turn-off Fall Time	t_f		--	18	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ C$	--	--	6	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ C, I_{SD} = 3A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Charge	Q_{rr}	$I_F = 3A, V_{GS} = 0V$ $di/dt=100A/us$	--	8	--	μC
Reverse Recovery Time	T_{rr}		--	1200	--	ns

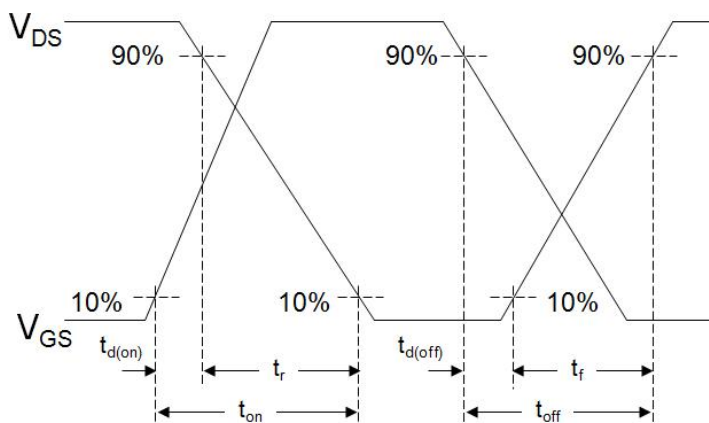
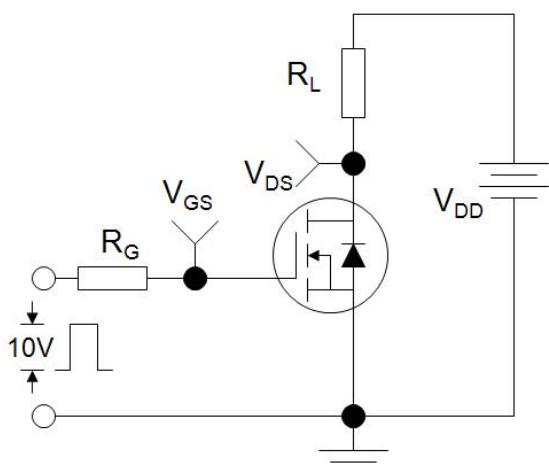
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_J = 25^\circ\text{C}, V_{DD} = 50V, V_{GS} = 10V, L = 10mH, R_G = 25\Omega$
The table shows the minimum avalanche energy, which is 500mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

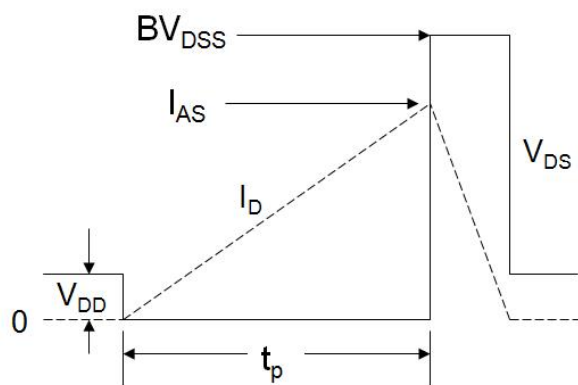
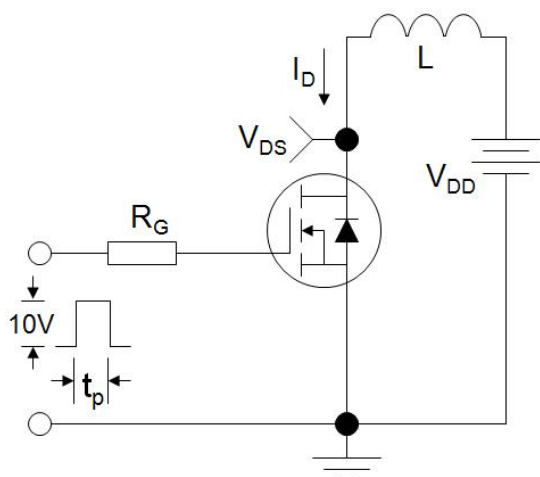
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

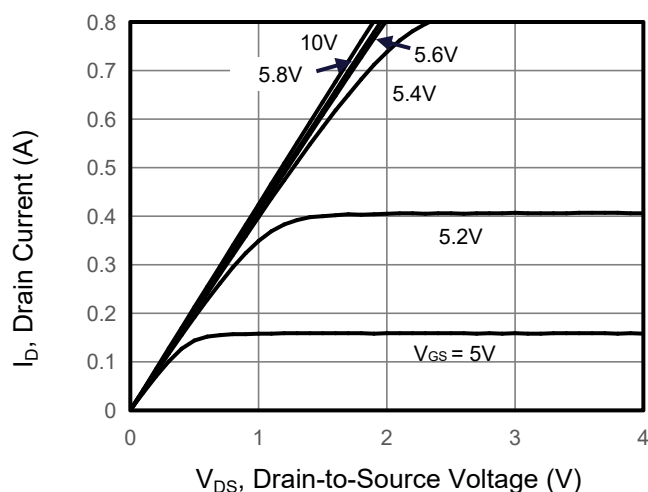


Figure 2. Transfer Characteristics

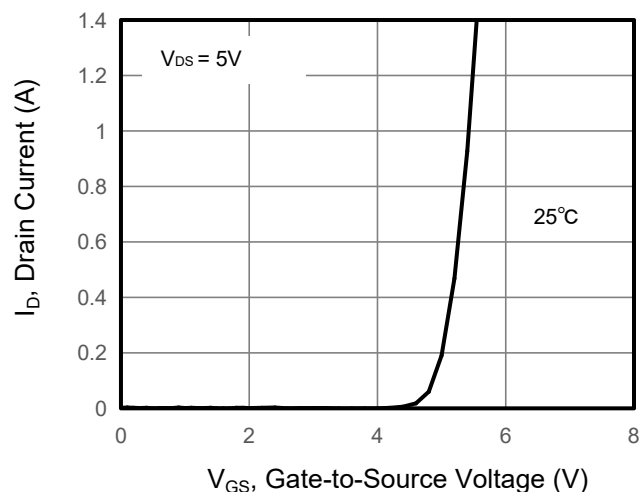


Figure 3. Drain Source On Resistance

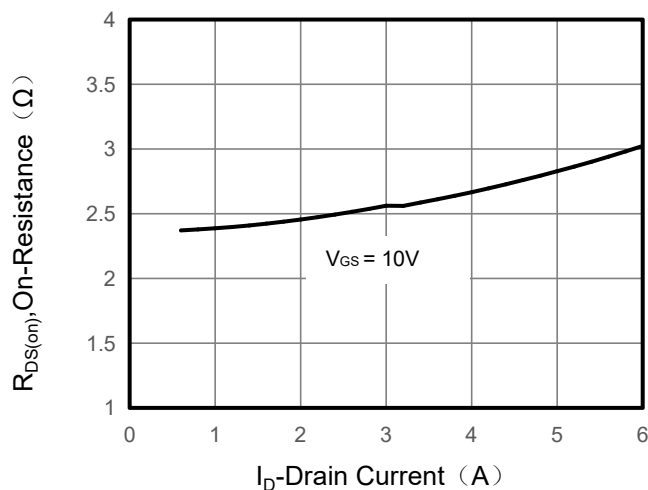


Figure 4. Gate Charge

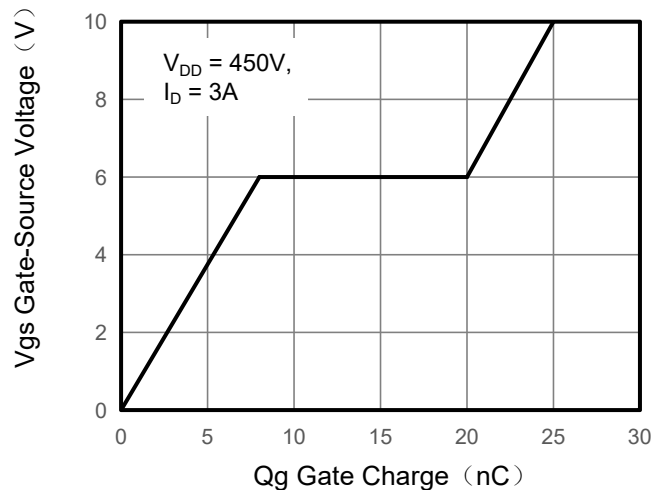


Figure 5. Capacitance

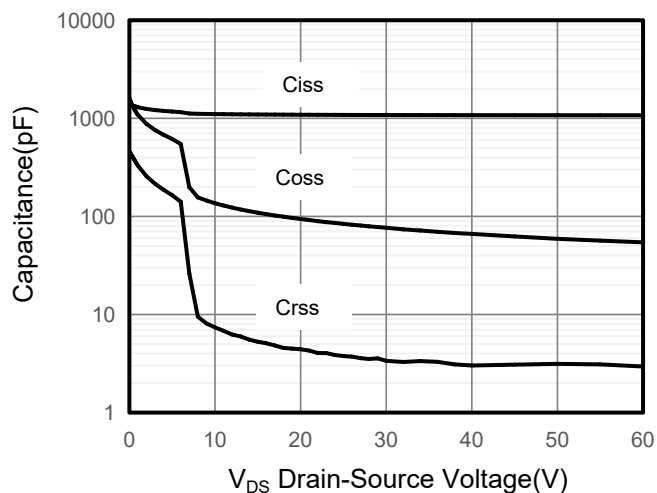
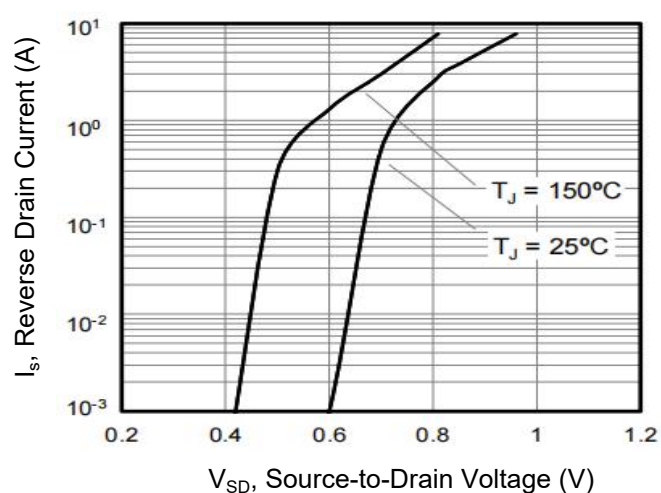


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

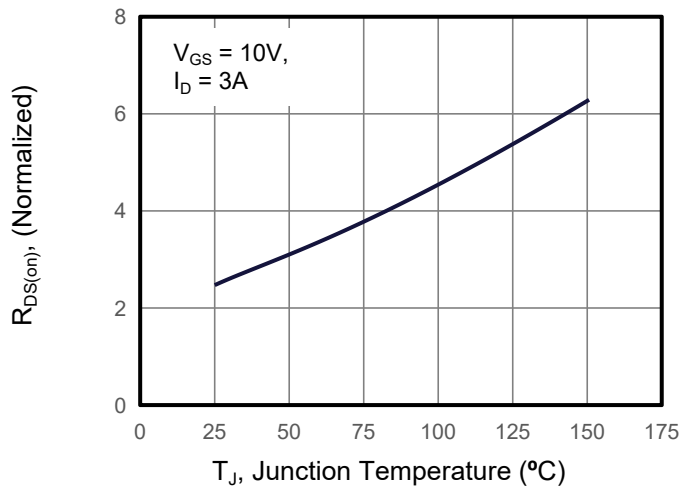


Figure 8. Safe Operation Area

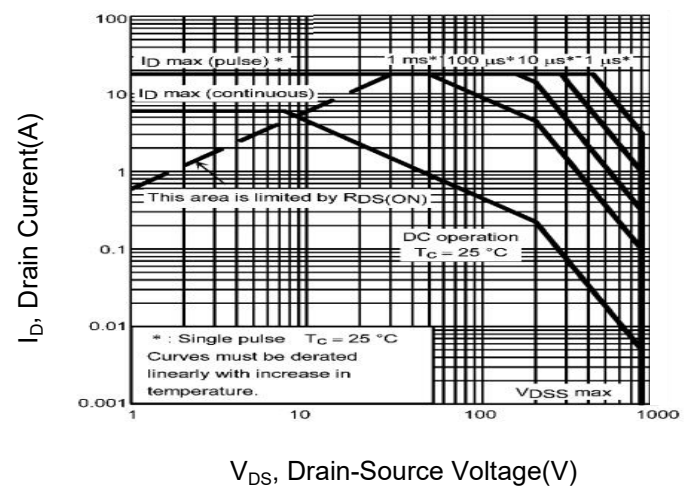
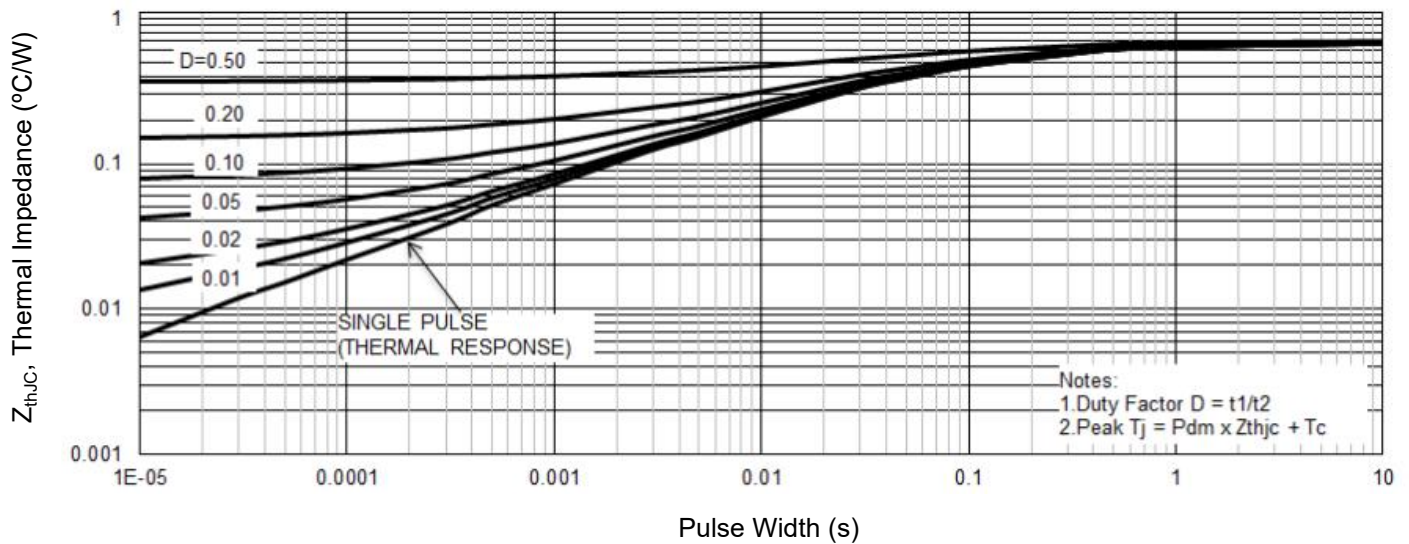
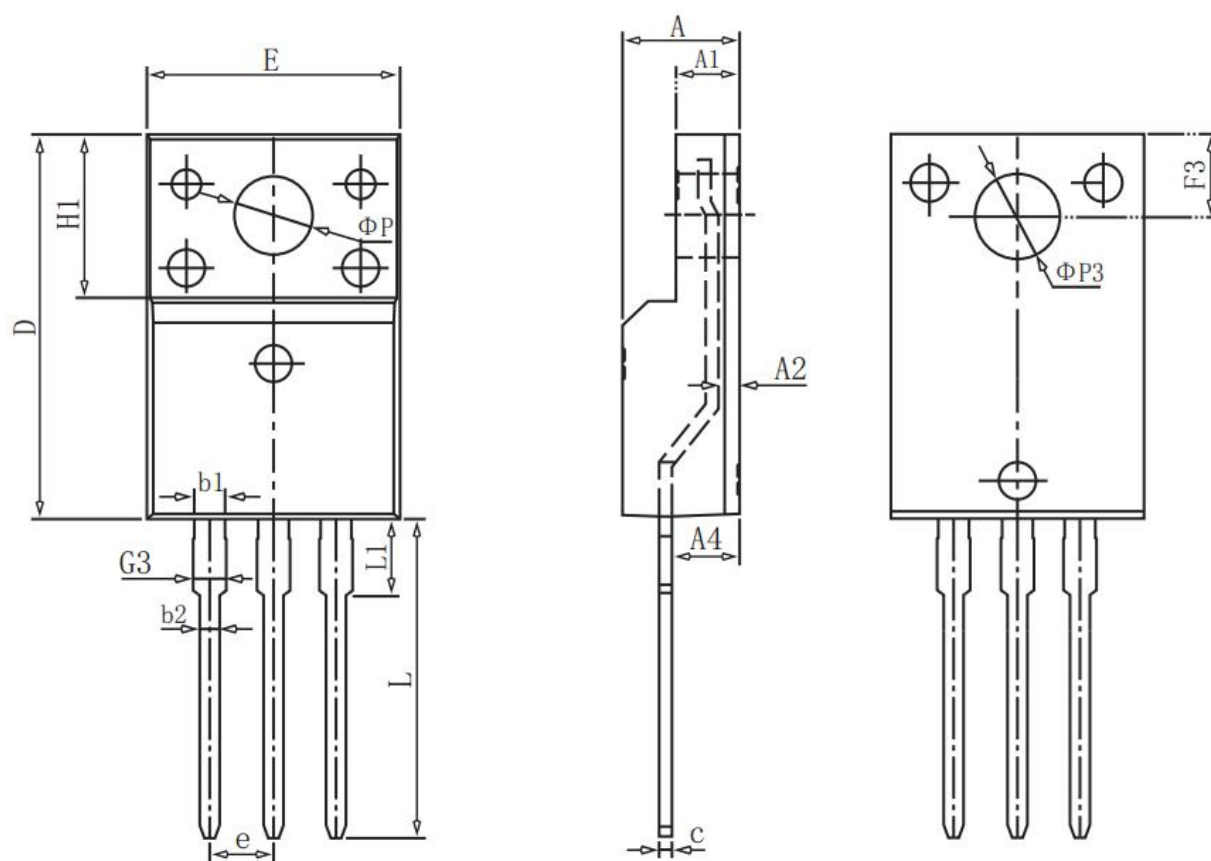


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-220F Package Information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
E	10.00	10.20	10.40
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.65	0.85	1.30
A4	2.55	2.75	2.95
c	0.40	0.50	0.65
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
ΦP	3.183REF		
L	12.68	12.98	13.28
L1	3.25	3.45	3.65
$\Phi P3$	3.45REF		
F3	3.10	3.30	3.50
G3	1.10	1.30	1.50
b1	1.05	1.20	1.35
b2	0.70	0.80	0.92